Jinn-Kong Sheu

List of Publications by Year
in descending order

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321 papers	7,091 citations	61984 43 h-index	91884 69 g-index
321 all docs	321 docs citations	321 times ranked	4631 citing authors

#	Article	IF	Citations
1	White-light emission from near UV InGaN-GaN LED chip precoated with blue/green/red phosphors. IEEE Photonics Technology Letters, 2003, 15, 18-20.	2.5	607
2	400-nm InGaN-GaN and InGaN-AlGaN multiquantum well light-emitting diodes. IEEE Journal of Selected Topics in Quantum Electronics, 2002, 8, 744-748.	2.9	213
3	Effects of thermal annealing on the indium tin oxide Schottky contacts of n-GaN. Applied Physics Letters, 1998, 72, 3317-3319.	3.3	150
4	Influence of Si-doping on the characteristics of InGaN-GaN multiple quantum-well blue light emitting diodes. IEEE Journal of Quantum Electronics, 2002, 38, 446-450.	1.9	147
5	GaN metal-semiconductor-metal ultraviolet photodetectors with transparent indium-tin-oxide Schottky contacts. IEEE Photonics Technology Letters, 2001, 13, 848-850.	2.5	144
6	Low-operation voltage of InGaN-GaN light-emitting diodes with Si-doped In/sub 0.3/Ga/sub 0.7/N/GaN short-period superlattice tunneling contact layer. IEEE Electron Device Letters, 2001, 22, 460-462.	3.9	125
7	InGaN-AlInGaN multiquantum-well LEDs. IEEE Photonics Technology Letters, 2001, 13, 559-561.	2.5	100
8	GaN metal-semiconductor-metal ultraviolet sensors with various contact electrodes. IEEE Sensors Journal, 2002, 2, 366-371.	4.7	99
9	Nitride-Based LEDs With 800<tex>$^circboxC$</tex>Grown p-AlInGaNâ€“GaN Double-Cap Layers. IEEE Photonics Technology Letters, 2004, 16, 1447-1449.	2.5	95
10	The doping process and dopant characteristics of GaN. Journal of Physics Condensed Matter, 2002, 14, R657-R702.	1.8	93
11	GaN metal-semiconductor-metal photodetectors with low-temperature-GaN cap layers and ITO metal contacts. IEEE Electron Device Letters, 2003, 24, 212-214.	3.9	93
12	n-UV+Blue/Green/Red White Light Emitting Diode Lamps. Japanese Journal of Applied Physics, 2003, 42, 2284-2287.	1.5	90
13	White-light emission from InGaN-GaN multiquantum-well light-emitting diodes with Si and Zn codoped active well layer. IEEE Photonics Technology Letters, 2002, 14, 450-452.	2.5	86
14	Enhanced efficiency of GaN-based light-emitting diodes with periodic textured Ga-doped ZnO transparent contact layer. Applied Physics Letters, 2007, 90, 263511.	3.3	83
15	Nitride-based cascade near white light-emitting diodes. IEEE Photonics Technology Letters, 2002, 14, 908-910.	2.5	77
16	Nonalloyed Crâˆ•Au-based Ohmic contacts to n-GaN. Applied Physics Letters, 2007, 91, .	3.3	74
17	Enhanced light output of GaN-based power LEDs with transparent Al-doped ZnO current spreading layer. IEEE Photonics Technology Letters, 2006, 18, 274-276.	2.5	72
18	Nitride-Based LEDs With an SPS Tunneling Contact Layer and an ITO Transparent Contact. IEEE Photonics Technology Letters, 2004, 16, 1002-1004.	2.5	70

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19	Lateral epitaxial patterned sapphire InGaN/GaN MQW LEDs. Journal of Crystal Growth, 2004, 261, 466-470.	1.5	67
20	Nitride-based light emitting diodes with indium tin oxide electrode patterned by imprint lithography. Applied Physics Letters, 2007, 91, 013504.	3.3	67
21	High efficiency and improved ESD characteristics of GaN-based LEDs with naturally textured surface grown by MOCVD. IEEE Photonics Technology Letters, 2006, 18, 1213-1215.	2.5	66
22	Ohmic contacts to p-type GaN mediated by polarization fields in thin InxGa1â^'xN capping layers. Applied Physics Letters, 2002, 80, 986-988.	3.3	65
23	Demonstration of GaN-Based Solar Cells With GaN/InGaN Superlattice Absorption Layers. IEEE Electron Device Letters, 2009, 30, 225-227.	3.9	65
24	Improved ESD protection by combining InGaN-GaN MQW LEDs with GaN Schottky diodes. IEEE Electron Device Letters, 2003, 24, 129-131.	3.9	63
25	Enhanced AlGaN/GaN MOS-HEMT Performance by Using Hydrogen Peroxide Oxidation Technique. IEEE Transactions on Electron Devices, 2013, 60, 213-220.	3.0	62
26	Effect of Thermal Annealing on Ga-Doped ZnO Films Prepared by Magnetron Sputtering. Journal of the Electrochemical Society, 2007, 154, H521.	2.9	61
27	InGaN/GaN light emitting diodes activated in O/sub 2/ ambient. IEEE Electron Device Letters, 2002, 23, 240-242.	3.9	60
28	High-Speed GaN-Based Green Light-Emitting Diodes With Partially n-Doped Active Layers and Current-Confined Apertures. IEEE Electron Device Letters, 2008, 29, 158-160.	3.9	60
29	High-efficiency InGaN-GaN MQW green light-emitting diodes with CART and DBR structures. IEEE Journal of Selected Topics in Quantum Electronics, 2002, 8, 284-288.	2.9	59
30	In0.23Ga0.77N/GaN MQW LEDs with a low temperature GaN cap layer. Solid-State Electronics, 2003, 47, 2027-2030.	1.4	58
31	ICP etching of sapphire substrates. Optical Materials, 2005, 27, 1171-1174.	3.6	58
32	Carrier dynamics in nitride-based light-emitting p-n junction diodes with two active regions emitting at different wavelengths. Journal of Applied Physics, 2003, 94, 2167-2172.	2.5	57
33	Effect of low-temperature-grown GaN cap layer on reduced leakage current of GaN Schottky diodes. Applied Physics Letters, 2005, 86, 052103.	3.3	53
34	Enhanced output power in GaN-based LEDs with naturally textured surface grown by MOCVD. IEEE Electron Device Letters, 2005, 26, 464-466.	3.9	53
35	High brightness green light emitting diodes with charge asymmetric resonance tunneling structure. IEEE Electron Device Letters, 2002, 23, 130-132.	3.9	52
36	n+-GaN formed by Si implantation intop-GaN. Journal of Applied Physics, 2002, 91, 1845-1848.	2.5	52

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37	InGaN/GaN tunnel-injection blue light-emitting diodes. IEEE Transactions on Electron Devices, 2002, 49, 1093-1095.	3.0	52
38	Nitride-based near-ultraviolet LEDs with an ITO transparent contact. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2004, 106, 69-72.	3.5	52
39	Enhancement in light output of InGaN-based microhole array light-emitting diodes. IEEE Photonics Technology Letters, 2005, 17, 1163-1165.	2.5	50
40	A curvature-tunable random laser. Nanoscale, 2019, 11, 3534-3545.	5.6	50
41	GaN Schottky barrier photodetectors with a low-temperature GaN cap layer. Applied Physics Letters, 2003, 82, 2913-2915.	3.3	46
42	Schottky barrier heights of metal contacts to n-type gallium nitride with low-temperature-grown cap layer. Applied Physics Letters, 2006, 88, 032103.	3.3	45
43	Probing Hydrophilic Interface of Solid/Liquid-Water by Nanoultrasonics. Scientific Reports, 2014, 4, 6249.	3.3	45
44	Low-operation voltage of InGaN/GaN light-emitting diodes by using a Mg-doped Al/sub 0.15/Ga/sub 0.85/N/GaN superlattice. IEEE Electron Device Letters, 2001, 22, 160-162.	3.9	44
45	Electroluminescence efficiency of blue InGaNâˆ•GaN quantum-well diodes with and without an n-InGaN electron reservoir layer. Journal of Applied Physics, 2006, 100, 113105.	2.5	44
46	THz acoustic phonon spectroscopy and nanoscopy by using piezoelectric semiconductor heterostructures. Ultrasonics, 2015, 56, 52-65.	3.9	44
47	InGaN light-emitting diodes with naturally formed truncated micropyramids on top surface. Applied Physics Letters, 2006, 88, 113505.	3.3	43
48	Enhancement in output power of blue gallium nitride-based light-emitting diodes with omnidirectional metal reflector under electrode pads. Applied Physics Letters, 2008, 93, 103507.	3.3	43
49	Planar GaN n+â€“p photodetectors formed by Si implantation into p-GaN. Applied Physics Letters, 2002, 81, 4263-4265.	3.3	42
50	GaN-Based Miniaturized Cyan Light-Emitting Diodes on a Patterned Sapphire Substrate With Improved Fiber Coupling for Very High-Speed Plastic Optical Fiber Communication. IEEE Photonics Journal, 2012, 4, 1520-1529.	2.0	42
51	Investigation of the mechanism for Ti/Al ohmic contact on etched n-GaN surfaces. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2000, 18, 729.	1.6	39
52	Enhanced output power in an InGaN-GaN multiquantum-well light-emitting diode with an InGaN current-spreading layer. IEEE Photonics Technology Letters, 2001, 13, 1164-1166.	2.5	39
53	High-performance GaN metalâ€“insulatorâ€“semiconductor ultraviolet photodetectors using gallium oxide as gate layer. Optics Express, 2011, 19, 12658.	3.4	39
54	Nitride-Based LEDs With Modulation-Doped Al<tex>$_0.12hbox Ga_0.88 hbox N$</tex>â€“GaN Superlattice Structures. IEEE Transactions on Electron Devices, 2004, 51, 1743-1746.	3.0	38

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55	Effect of Thickness of the p-AlGaN Electron Blocking Layer on the Improvement of ESD Characteristics in GaN-Based LEDs. IEEE Photonics Technology Letters, 2008, 20, 1142-1144.	2.5	38
56	Improvement of near-ultraviolet InGaN-GaN light-emitting diodes with an AlGaN electron-blocking layer grown at low temperature. IEEE Photonics Technology Letters, 2003, 15, 1342-1344.	2.5	37
57	Characterization of GaN Schottky barrier photodetectors with a low-temperature GaN cap layer. Journal of Applied Physics, 2003, 94, 1753-1757.	2.5	37
58	Reduction of Dark Current in AlGaNâ€“GaN Schottky-Barrier Photodetectors With a Low-Temperature-Grown GaN Cap Layer. IEEE Electron Device Letters, 2004, 25, 593-595.	3.9	37
59	Improved Reliability and ESD Characteristics of Flip-Chip GaN-Based LEDs With Internal Inverse-Parallel Protection Diodes. IEEE Electron Device Letters, 2007, 28, 346-349.	3.9	37
60	Laser-induced periodic structures for light extraction efficiency enhancement of GaN-based light emitting diodes. Optics Express, 2012, 20, 5689.	3.4	36
61	Indium tin oxide ohmic contact to highly doped n-GaN. Solid-State Electronics, 1999, 43, 2081-2084.	1.4	35
62	Emission Mechanism of Mixed-Color InGaN/GaN Multi-Quantum-Well Light-Emitting Diodes. Japanese Journal of Applied Physics, 2006, 45, 2463-2466.	1.5	35
63	Characterization of Si implants in p-type GaN. IEEE Journal of Selected Topics in Quantum Electronics, 2002, 8, 767-772.	2.9	34
64	Improved Performance of GaN-Based Blue LEDs With the InGaN Insertion Layer Between the MQW Active Layer and the n-GaN Cladding Layer. IEEE Journal of Quantum Electronics, 2010, 46, 513-517.	1.9	34
65	Luminescence of an InGaN/GaN multiple quantum well light-emitting diode. Solid-State Electronics, 2000, 44, 1055-1058.	1.4	32
66	The improvement in modulation speed of GaN-based Green light-emitting diode (LED) by use of n-type barrier doping for plastic optical fiber (POF) communication. IEEE Photonics Technology Letters, 2006, 18, 1636-1638.	2.5	32
67	Ga-Doped ZnO Transparent Conductive Oxide Films Applied to GaN-Based Light-Emitting Diodes for Improving Light Extraction Efficiency. IEEE Journal of Quantum Electronics, 2008, 44, 1211-1218.	1.9	32
68	Design of Hole-Blocking and Electron-Blocking Layers in Al_xGa_{1-x}N-Based UV Light-Emitting Diodes. IEEE Transactions on Electron Devices, 2016, 63, 1141-1147.	3.0	32
69	InGaN-based epitaxial films as photoelectrodes for hydrogen generation through water photoelectrolysis and CO2 reduction to formic acid. Solar Energy Materials and Solar Cells, 2017, 166, 86-90.	6.2	32
70	Si and Zn co-doped InGaN-GaN white light-emitting diodes. IEEE Transactions on Electron Devices, 2003, 50, 519-521.	3.0	31
71	Improving efficiency of InGaN/GaN multiple quantum well solar cells using CdS quantum dots and distributed Bragg reflectors. Solar Energy Materials and Solar Cells, 2013, 117, 531-536.	6.2	31
72	Sea-Urchin-Like Bi₂S₃ Microstructures Decorated with Graphitic Carbon Nitride Nanosheets for Use in Food Preservation. ACS Applied Nano Materials, 2022, 5, 2375-2384.	5.0	31

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73	Ultraviolet band-pass Schottky barrier photodetectors formed by Al-doped ZnO contacts to n-GaN. Applied Physics Letters, 2006, 88, 043506.	3.3	30
74	Effect of the Electrode Pattern on Current Spreading and Driving Voltage in a GaNâˆ•Sapphire LED Chip. Journal of the Electrochemical Society, 2008, 155, H836.	2.9	30
75	III-Nitride Based Cyan Light-Emitting Diodes with GHz Bandwidth for High-Speed Visible Light Communication. IEEE Electron Device Letters, 2016, , 1-1.	3.9	30
76	GaN-based p-i-n sensors with ITO contacts. IEEE Sensors Journal, 2006, 6, 406-411.	4.7	29
77	High brightness ingan green leds with an ito on n/sup ++/ -sps upper contact. IEEE Transactions on Electron Devices, 2003, 50, 2208-2212.	3.0	28
78	Inverted Al0.25Ga0.75N/GaN ultraviolet p-i-n photodiodes formed on p-GaN template layer grown by metalorganic vapor phase epitaxy. Applied Physics Letters, 2010, 97, 013502.	3.3	27
79	GaN-based light emitting diodes with embedded SiO2 pillars and air gap array structures. Applied Physics Letters, 2010, 97, .	3.3	27
80	Enhancement of the conversion efficiency of GaN-based photovoltaic devices with AlGaN/InGaN absorption layers. Applied Physics Letters, 2010, 97, 021113.	3.3	27
81	Slanted n-ZnO/p-GaN nanorod arrays light-emitting diodes grown by oblique-angle deposition. APL Materials, 2014, 2, 056101.	5.1	27
82	Enhancing UV-emissions through optical and electronic dual-function tuning of Ag nanoparticles hybridized with n-ZnO nanorods/p-GaN heterojunction light-emitting diodes. Nanoscale, 2016, 8, 4463-4474.	5.6	27
83	Ultraviolet bandpass Al0.17Ga0.83Nâˆ•GaN heterojunction phototransitors with high optical gain and high rejection ratio. Applied Physics Letters, 2008, 92, .	3.3	26
84	Effects of Thermal Annealing on Al-Doped ZnO Films Deposited on p-Type Gallium Nitride. Journal of the Electrochemical Society, 2006, 153, G296.	2.9	25
85	Photodetectors formed by an indium tin oxide/zinc oxide/p-type gallium nitride heterojunction with high ultraviolet-to-visible rejection ratio. Applied Physics Letters, 2009, 94, 013512.	3.3	25
86	Low Operation Voltage of Nitride-Based LEDs with Al-Doped ZnO Transparent Contact Layer. Electrochemical and Solid-State Letters, 2008, 11, H269.	2.2	24
87	A Numerical Study of Thermal and Electrical Effects in a Vertical LED Chip. Journal of the Electrochemical Society, 2010, 157, H31.	2.9	24
88	Rationally designed RGO@CuO@Mn₂O₃as an excellent electrocatalyst for the rapid and real-time detection of 2-nitrophenol. New Journal of Chemistry, 2020, 44, 12465-12472.	2.8	24
89	Nitride-based green light-emitting diodes with high temperature GaN barrier layers. IEEE Transactions on Electron Devices, 2003, 50, 1766-1770.	3.0	23
90	Ga₂O₃Films for Photoelectrochemical Hydrogen Generation. Journal of the Electrochemical Society, 2014, 161, H508-H511.	2.9	23

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91	White emission from non-planar InGaN/GaN MQW LEDs grown on GaN template with truncated hexagonal pyramids. Optics Express, 2015, 23, A401.	3.4	23
92	Observation of dislocation etch pits in epitaxial lateral overgrowth GaN by wet etching. Solid-State Electronics, 2002, 46, 555-558.	1.4	22
93	Femtosecond ultrasonic spectroscopy using a piezoelectric nanolayer: Hypersound attenuation in vitreous silica films. Applied Physics Letters, 2011, 99, 051913.	3.3	22
94	Nitride-based blue LEDs with GaN/SiN double buffer layers. Solid-State Electronics, 2003, 47, 2019-2022.	1.4	21
95	InGaN gallium nitride light-emitting diodes with reflective electrode pads and textured gallium-doped ZnO contact layer. Applied Physics Letters, 2010, 96, 133504.	3.3	21
96	Light-emitting diodes with surface gallium nitride pâ€“n homojunction structure formed by selective area regrowth. Scientific Reports, 2019, 9, 3243.	3.3	21
97	GaN pâ€“n junction diode formed by Si ion implantation into p-GaN. Solid-State Electronics, 2002, 46, 2179-2183.	1.4	20
98	Deep level defect in Si-implanted GaNâ€Šn+-p junction. Applied Physics Letters, 2003, 82, 3671-3673.	3.3	20
99	Experimental study of perpendicular transport in weakly coupled AlxGa1â^'xN/GaN superlattices. Applied Physics Letters, 2003, 83, 4975-4977.	3.3	20
100	Comparison of low-temperature GaN, SiO2, and SiNx as gate insulators on AlGaNâ•GaN heterostructure field-effect transistors. Journal of Applied Physics, 2005, 98, 064506.	2.5	20
101	Electrical-optical analysis of a GaN/sapphire LED chip by considering the resistivity of the current-spreading layer. Optical Review, 2009, 16, 213-215.	2.0	20
102	Vertical InGaN-based green-band solar cells operating under high solar concentration up to 300 suns. Optics Express, 2014, 22, A1222.	3.4	20
103	Ultraviolet/blue light-emitting diodes based on single horizontal ZnO microrod/GaN heterojunction. Nanoscale Research Letters, 2014, 9, 446.	5.7	20
104	Mn valence state mediated room temperature ferromagnetism in nonpolar Mn doped GaN. Applied Surface Science, 2019, 473, 693-698.	6.1	20
105	Visibleâ€“blind GaN pâ€“iâ€“n photodiodes with an Al0.12Ga0.88N/GaN superlattice structure. Solid-State Electronics, 2003, 47, 873-878.	1.4	19
106	Phosphor-Free GaN-Based Transverse Junction Light Emitting Diodes for the Generation of White Light. IEEE Photonics Technology Letters, 2006, 18, 2593-2595.	2.5	19
107	AlGaN ultraviolet metal-semiconductor-metal photodetectors grown on Si substrates. Sensors and Actuators A: Physical, 2007, 135, 502-506.	4.1	19
108	GaN-Based LEDs With AZO:Y Upper Contact. IEEE Transactions on Electron Devices, 2010, 57, 134-139.	3.0	19

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109	Improved conversion efficiency of GaN-based solar cells with Mn-doped absorption layer. Applied Physics Letters, 2013, 103, 063906.	3.3	19
110	Passively gain-switched and self mode-locked thulium fiber laser at 1950nm. Optics and Laser Technology, 2014, 56, 354-357.	4.6	19
111	Polymer PBT/n-GaN metalâ€“insulatorâ€“semiconductor structure. Applied Physics Letters, 2001, 79, 4589-4591.	3.3	18
112	High-Responsivity Solar-Blind Photodetectors Formed by Ga₂O₃/p-GaN Bipolar Heterojunctions. ACS Photonics, 2022, 9, 1002-1007.	6.6	18
113	Temperature-dependent study of n-ZnOâˆ•p-GaN diodes. Applied Physics Letters, 2007, 90, 132111.	3.3	17
114	Ultraviolet band-pass photodetectors formed by Ga-doped ZnO contacts to n-GaN. Applied Physics Letters, 2008, 92, 113512.	3.3	17
115	Characteristics of InGaN-based concentrator solar cells operating under 150X solar concentration. Optics Express, 2011, 19, A695.	3.4	17
116	Thermal Boundary Resistance between GaN and Cubic Ice and THz Acoustic Attenuation Spectrum of Cubic Ice from Complex Acoustic Impedance Measurements. Physical Review Letters, 2013, 111, 225901.	7.8	17
117	AlGaN-based deep ultraviolet light emitting diodes with magnesium delta-doped AlGaN last barrier. Applied Physics Letters, 2020, 117, .	3.3	17
118	Low-resistance Ni/Au ohmic contact to Mg-doped of Al0.15Ga0.85N/GaN superlattices. Solid-State Electronics, 2001, 45, 717-720.	1.4	16
119	Effect of Cl2âˆ•Ar dry etching on p-GaN with Niâˆ•Au metallization characterization. Applied Physics Letters, 2005, 87, 252107.	3.3	16
120	Improved Output Power of GaN-based Blue LEDs by Forming Air Voids on Ar-Implanted Sapphire Substrate. Journal of Lightwave Technology, 2013, 31, 1318-1322.	4.6	16
121	Warm-white light-emitting diode with high color rendering index fabricated by combining trichromatic InGaN emitter with single red phosphor. Optics Express, 2015, 23, A232.	3.4	16
122	Manganese-doped AlGaN/GaN heterojunction solar cells with intermediate band absorption. Solar Energy Materials and Solar Cells, 2016, 157, 727-732.	6.2	16
123	Linear Cascade Arrays of GaN-Based Green Light-Emitting Diodes for High-Speed and High-Power Performance. IEEE Photonics Technology Letters, 2007, 19, 1368-1370.	2.5	15
124	Improvement of InGaN/GaN laser diodes by using a Si-doped In/sub 0.23/Ga/sub 0.77/N/GaN short-period superlattice tunneling contact layer. IEEE Electron Device Letters, 2003, 24, 206-208.	3.9	14
125	Si diffusion in p-GaN. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2004, 22, 1727.	1.6	14
126	Investigation of the Carrier Dynamic in GaN-Based Cascade Green Light-Emitting Diodes Using the Very Fast Electricalâ€“Optical Pumpâ€“Probe Technique. IEEE Transactions on Electron Devices, 2011, 58, 495-500.	3.0	14

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127	Mn-doped GaN as photoelectrodes for the photoelectrolysis of water under visible light. Optics Express, 2012, 20, A678.	3.4	14
128	GaN-Based Planar p-i-n Photodetectors With the Be-Implanted Isolation Ring. IEEE Transactions on Electron Devices, 2013, 60, 1178-1182.	3.0	14
129	High-power and single-mode VCSEL arrays with single-polarized outputs by using package-induced tensile strain. Optics Letters, 2020, 45, 4839.	3.3	14
130	Highly Reliable Nitride-Based LEDs With Internal ESD Protection Diodes. IEEE Transactions on Device and Materials Reliability, 2006, 6, 442-447.	2.0	13
131	Improved performance of planar GaN-based p-i-n photodetectors with Mg-implanted isolation ring. Applied Physics Letters, 2006, 89, 183509.	3.3	13
132	AlGaN/GaN Schottky-barrier UV-B bandpass photodetectors with ITO contacts and LT-GaN cap layers. Semiconductor Science and Technology, 2006, 21, 1064-1068.	2.0	13
133	Phosphor-Free GaN-Based Transverse Junction White-Light Light-Emitting Diodes With Regrown n-Type Regions. IEEE Photonics Technology Letters, 2008, 20, 449-451.	2.5	13
134	GaN-Based LEDs Output Power Improved by Textured GaN/Sapphire Interface Using <emphasis emphasistype="italic">In Situ</emphasis> <formula formulatype="inline"><tex Notation="TeX">$hbox{SiH}_{f 4}$</tex> </formula> Treatment Process During Epitaxial Growth. IEEE Journal of Selected Topics in Quantum Electronics, 2009, 15, 1275-1280.	2.9	13
135	Hydrogen gas generation using n-GaN photoelectrodes with immersed Indium Tin Oxide ohmic contacts. Optics Express, 2011, 19, A1196.	3.4	13
136	Femtosecond excitation of radial breathing mode in 2-D arrayed GaN nanorods. Optics Express, 2012, 20, 16611.	3.4	13
137	GaN-based light emitting diodes with micro- and nano-patterned structures by femtosecond laser nonlinear decomposition. Applied Physics Letters, 2012, 101, 131103.	3.3	13
138	Characterization of p-type InxGa1âˆ’xN grown by metalorganic chemical vapor deposition. Solid-State Electronics, 2001, 45, 427-430.	1.4	12
139	Linear Cascade GaN-Based Green Light-Emitting Diodes With Invariant High-Speed/Power Performance Under High-Temperature Operation. IEEE Photonics Technology Letters, 2008, 20, 1896-1898.	2.5	12
140	High-Brightness InGaNâ€“GaN Power Flip-Chip LEDs. Journal of Lightwave Technology, 2009, 27, 1985-1989.	4.6	12
141	Femtosecond laser-ultrasonic investigation of plasmonic fields on the metal/gallium nitride interface. Applied Physics Letters, 2010, 97, .	3.3	12
142	Effect of Growth Pressure of Undoped GaN Layer on the ESD Characteristics of GaN-Based LEDs Grown on Patterned Sapphire. IEEE Photonics Technology Letters, 2011, 23, 968-970.	2.5	12
143	Influence of modulated fields on the Landau level properties of graphene. Physical Review B, 2011, 83, .	3.2	12
144	Gallium nitride-based light-emitting diodes with embedded air voids grown on Ar-implanted AlN/sapphire substrate. Applied Physics Letters, 2012, 101, .	3.3	12

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145	InGaN working electrodes with assisted bias generated from GaAs solar cells for efficient water splitting. Optics Express, 2013, 21, A991.	3.4	12
146	In Situ Monitoring of Chemical Reactions at a Solidâ€“Water Interface by Femtosecond Acoustics. Journal of Physical Chemistry Letters, 2017, 8, 5430-5437.	4.6	12
147	AlGaInP/GaP Light-Emitting Diodes Fabricated by Wafer Direct Bonding Technology. Japanese Journal of Applied Physics, 1996, 35, 4199-4202.	1.5	11
148	GaN diffractive microlenses fabricated with gray-level mask. Optics Communications, 2003, 215, 75-78.	2.1	11
149	GaInN light-emitting diodes with omnidirectional reflectors. , 2003, 4996, 139.		11
150	Improved Light Extraction Efficiency in AlGaInP Light-Emitting Diodes by Applying a Periodic Texture on the Surface. IEEE Photonics Technology Letters, 2008, 20, 1724-1726.	2.5	11
151	The Structure of GaN-Based Transverse Junction Blue LED Array for Uniform Distribution of Injected Current/Carriers. IEEE Journal of Selected Topics in Quantum Electronics, 2009, 15, 1292-1297.	2.9	11
152	Improved Hydrogen Gas Generation Rate of n-GaN Photoelectrode with SiO[sub 2] Protection Layer on the Ohmic Contacts from the Electrolyte. Journal of the Electrochemical Society, 2010, 157, B266.	2.9	11
153	Vertical InGaN light-emitting diodes with a sapphire-face-up structure. Optics Express, 2012, 20, A119.	3.4	11
154	GaN-Based Cyan Light-Emitting Diode with up to 1-GHz Bandwidth for High-Speed Transmission Over SI-POF. IEEE Photonics Journal, 2017, 9, 1-7.	2.0	11
155	Planar GaN-Based Blue Light-Emitting Diodes With Surface p-n Junction Formed by Selective-Area Siâ€“Ion Implantation. IEEE Transactions on Electron Devices, 2017, 64, 4156-4160.	3.0	11
156	GaN intermediate band solar cells with Mn-doped absorption layer. Scientific Reports, 2018, 8, 8641.	3.3	11
157	Piezoelectric effect on Al0.35â^ÎInÎ´Ga0.65N/GaN heterostructures. Applied Physics Letters, 2002, 80, 2684-2686.	3.3	10
158	AlGaN-GaN Schottky-barrier photodetectors with LT GaN cap layers. Journal of Crystal Growth, 2005, 283, 68-71.	1.5	10
159	GaN-Based Light-Emitting Diodes With Pillar Structures Around the Mesa Region. IEEE Journal of Quantum Electronics, 2010, 46, 1066-1071.	1.9	10
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